

FDS6690

Single N-Channel Logic Level PWM Optimized PowerTrench® MOSFET

General Description

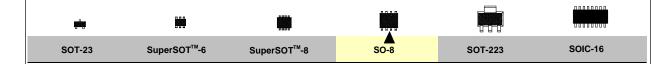
This N Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

The MOSFET features faster switching and lower gate charge than other MOSFETs with comparable $R_{\rm DS(ON)}$ specifications.

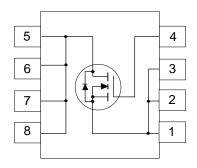
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 10 A, 30 V. $R_{DS(ON)} = 0.0135 \Omega$ @ $V_{GS} = 10 V$ $R_{DS(ON)} = 0.0200 \Omega$ @ $V_{GS} = 4.5 V$.
- Optimized for use in switching DC/DC converters with PWM controllers.
- Very fast switching .
- Low gate charge (Qg typ = 13 nC).





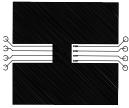


Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$ unless other wise noted

Symbol	Parameter		FDS6690	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
D	Drain Current - Continuous	(Note 1a)	10	А
	- Pulsed		50	
$P_{_{\rm D}}$	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T_J , T_{STG}	Operating and Storage Temperature Range	ge	-55 to 150	°C
THERMA	L CHARACTERISTICS	<u>.</u>		
R _{BJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R _{euc}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Symbol	Parameter	Min	Тур	Max	Units	
OFF CHAR	ACTERISTICS					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		21		mV /°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ V_{GS} = 0 \text{ V}$			1	μA
		T _J = 55°C			10	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
ON CHARA	CTERISTICS (Note 2)		,	•		,
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	2	3	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		-4.5		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 10 A		0.011	0.0135	Ω
,		T _J =125°C		0.018	0.023	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 9 \text{ A}$		0.017	0.02	
D(ON)	On-State Drain Current	$V_{GS} = 10 \text{ V}, \ V_{DS} = 5 \text{ V}$	50			Α
J _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		27		S
DYNAMIC	CHARACTERISTICS		•	•	•	•
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1340		pF
oss	Output Capacitance	f = 1.0 MHz		340		pF
C _{rss}	Reverse Transfer Capacitance			125		pF
WITCHING	G CHARACTERISTICS (Note 2)					
t _{D(on)}	Tum - On Delay Time	$V_{DS} = 15 \text{ V}, I_{D} = 1 \text{ A}$		12	22	ns
r	Turn - On Rise Time	$V_{GS} = 10 \text{ V}$, $R_{GEN} = 6\Omega$		13	24	ns
D(off)	Turn - Off Delay Time			38	60	ns
	Turn - Off Fall Time			10	18	ns
\mathbf{Q}_{g}	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A},$		13	18	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 5 V		5		nC
Q_{gd}	Gate-Drain Charge			4		nC
DRAIN-SOL	JRCE DIODE CHARACTERISTICS AND MAX	KIMUM RATINGS				
s	Maximum Continuous Drain-Source Diode Fo	rward Current			2.1	Α
/ _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.1 \text{ A} \text{ (Note 2)}$		0.73	1.2	V

1. R_{g,n} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{g,c} is guaranteed by design while R_{g,c,h} is determined by the user's board design.



a. 50°C/W on a 0.5 in² pad of 2oz copper.





Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

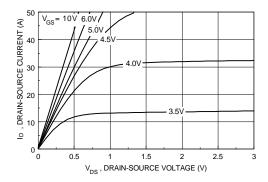


Figure 1. On-Region Characteristics.

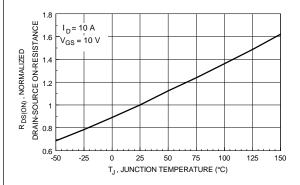


Figure 3. On-Resistance Variation with Temperature.

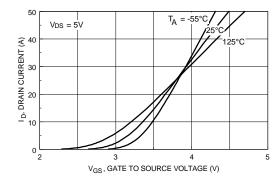


Figure 5. Transfer Characteristics.

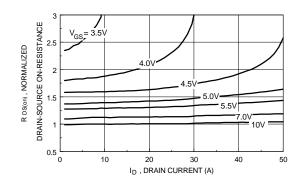


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

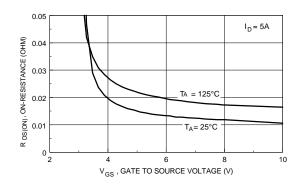


Figure 4 . On Resistance Variation with Gate-to-Source Voltage.

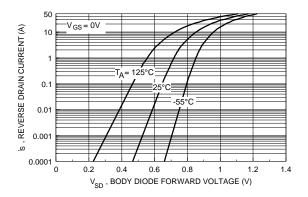


Figure 6 . Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical And Thermal Characteristics

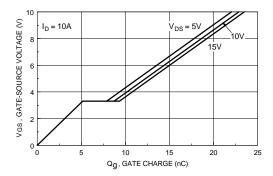


Figure 7. Gate Charge Characteristics.

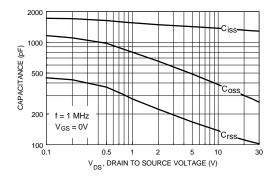


Figure 8. Capacitance Characteristics.

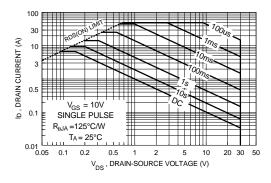


Figure 9. Maximum Safe Operating Area.

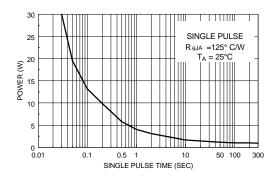


Figure 10. Single Pulse Maximum Power Dissipation.

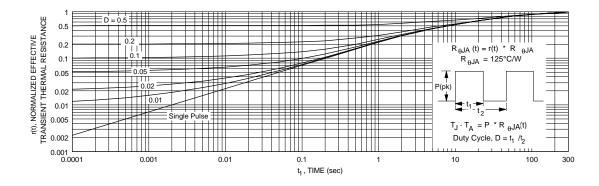
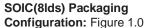


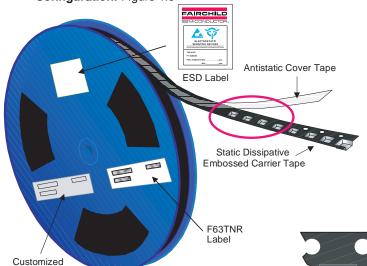
Figure 11. Transient Thermal Response Curve .

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions





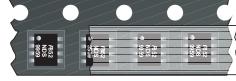


Packaging Description:

Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and amit-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 300cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (antistatic coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reles are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.





Packaging Option Standard o flow code) L86Z D84Z Rail/Tube TNR Packaging type TNR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 13" Dia 13" Dia 7" Dia 343y64y343 530x130x83 343y64y343 184v187v47 5,000 30,000 8,000 1,000

Box Dimension (mm) Max qty per Box Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC (8lds) Packaging Information

SOIC-8 Unit Orientation

F63TNR Label sample

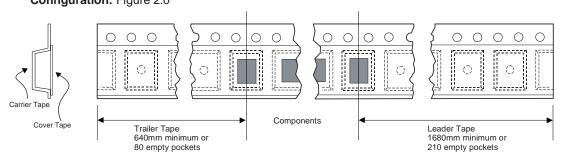
Label

Reel Size



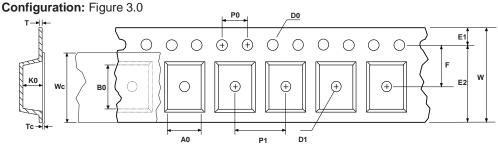
343mm x 342mm x 64mm Standard Intermediate box ESD Label F63TNL F63TN Label

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





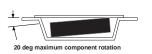
SOIC(8lds) Embossed Carrier Tape



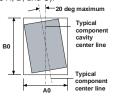


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

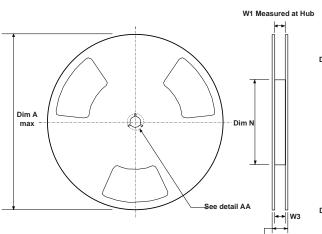
Component Rotation



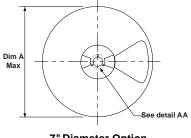
Sketch C (Top View)

Component lateral movement

SOIC(8lds) Reel Configuration: Figure 4.0



13" Diameter Option



7" Diameter Option

B Min

Dim C

Dim D

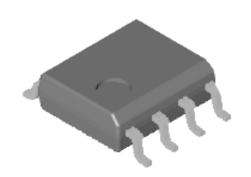
min

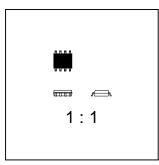
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

W2 max Measured at Hub

SO-8 Tape and Reel Data and Package Dimensions, continued

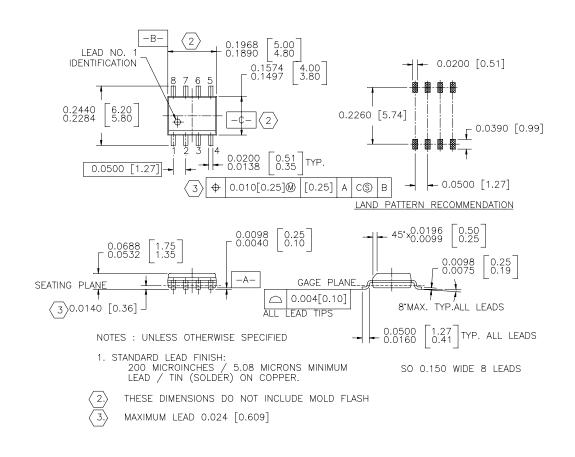
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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